*			<b>(4)</b>	
L Number	Hits	Search Text	DB ,	Time stamp
3	1385	(P\$2substrat\$3 ("P" adj3 tupe adj2	USPAT;	2001/08/03 17:00
]		substrate))	US-PGPUB	
4	17824	(P\$2source ("P" adj7 source))	USPAT;	2001/08/03 17:00
_	00550		US-PGPUB	
5	38650	gate adj3 electrode	USPAT;	2001/08/03 17:00
			US-PGPUB	
6	2772	(P\$3polysilicon ("P" adj8 polysilicon))	USPAT;	2001/08/03 17:01
			US-PGPUB	
7	433	((P\$2substrat\$3 ("P" adj3 tupe adj2	USPAT;	2001/08/03 16:19
		substrate))) and ((P\$2source ("P" adj7	US-PGPUB	
		source)))		
8	175	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2001/08/03 16:19
į		substrate))) and ((P\$2source ("P" adj7	US-PGPUB	
	2.7	source)))) and (gate adj3 electrode)		
9	37	((((P\$2substrat\$3 ("P" adj3 tupe adj2	USPAT;	2001/08/03 16:23
		substrate))) and ((P\$2source ("P" adj7	US-PGPUB	
		source)))) and (gate adj3 electrode)) and		
1.0	100015	((P\$3polysilicon ("P" adj8 polysilicon)))		
10	400245	substrate wafer	USPAT;	2001/08/03 17:01
1,,	161400		US-PGPUB	
11	161409	(substrate wafer ) and (dielectric	USPAT;	2001/08/03 17:02
1.0	E 3 4 5 .	insulat\$3 (silicon adj2 oxide))	US-PGPUB	0001/00/00
12	57134	((substrate wafer ) and (dielectric	USPAT;	2001/08/03 17:02
		insulat\$3 (silicon adj2 oxide))) and	US-PGPUB	
12	1 4005	(implant\$3 dop\$4)		0001 (00 (00 = =========================
13	14385	(((substrate wafer ) and (dielectric	USPAT;	2001/08/03 17:02
		insulat\$3 (silicon adj2 oxide))) and	US-PGPUB	
1.4	11242	(implant\$3 dop\$4)) and epitaxial		
14	11343	((((substrate wafer ) and (dielectric	USPAT;	2001/08/03 17:03
		insulat\$3 (silicon adj2 oxide))) and	US-PGPUB	
		(implant\$3 dop\$4)) and epitaxial) and		
1.5	10000	(boron "B")		
15	10399	(((((substrate wafer ) and (dielectric	USPAT;	2001/08/03 17:03
		insulat\$3 (silicon adj2 oxide))) and	US-PGPUB	
		(implant\$3 dop\$4)) and epitaxial) and		
126	0000	(boron "B")) and (phosphrous "P")		
16	2833	((((((substrate wafer ) and (dielectric	USPAT;	2001/08/03 17:04
		insulat\$3 (silicon adj2 oxide))) and	US-PGPUB	1
		(implant\$3 dop\$4)) and epitaxial) and		
		(boron "B")) and (phosphrous "P")) and		
		(P\$2channel\$2 ("P" adj2 channel) P?channel)		
17	1201		IIODAM.	2001 (00 (02 16 26
1 /	1381	(((((((substrate wafer) and (dielectric	USPAT;	2001/08/03 16:36
İ		insulat\$3 (silicon adj2 oxide))) and (implant\$3 dop\$4)) and epitaxial) and	US-PGPUB	
		(boron "B")) and (phosphrous "P")) and		
		(P\$2channel\$2 ("P" adj2 channel)		
		P?channel)) and anneal\$3		
18	351	(P\$2substrat\$3 ("P" adj3 tupe adj2	EPO; JPO;	2001/08/03 17:00
10	201	substrate))	DERWENT;	2001/08/03 17:00
		Judgetate//	IBM TDB	
19	7629	(P\$2source ("P" adj7 source))	EPO; JPO;	2001/08/03 17:00
	1023	(17200dice ( 1 adj. 30dice))	DERWENT;	2001/00/03 17:00
			IBM TDB	
20	73183	gato adi3 ologtrodo		2001/09/03 17:01
40	12183	gate adj3 electrode	EPO; JPO;	2001/08/03 17:01
			DERWENT;	7
21	1000	(Deamalwailiaan /UDU adio wallailiaan)	IBM TDB	2001/09/03 17:01
71	1220	(P\$3polysilicon ("P" adj8 polysilicon))	EPO; JPO;	2001/08/03 17:01
			DERWENT;	1
22	_	/ (DéCoubetmaté) / (IDH - 4-2 + 410	IBM TDB	2001/00/03 17 01
22	0	((P\$2substrat\$3 ("P" adj3 tupe adj2	EPO; JPO;	2001/08/03 17:01
		substrate))) and ((P\$2source ("P" adj7	DERWENT;	
		source))) and (gate adj3 electrode) and	IBM TDB	
33		((P\$3polysilicon ("P" adj8 polysilicon)))	770	0001/00/00 17 01
23	9		EPO; JPO;	2001/08/03 17:01
		substrate))) and ((P\$2source ("P" adj7	DERWENT;	
24	1004010	source))) and (gate adj3 electrode)	IBM TDB	2001/00/03 13 00
24	1094018	substrate wafer	EPO; JPO;	2001/08/03 17:02
			DERWENT;	
l			IBM TDB	

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25	236460	(substrate wafer ) and (dielectric	EPO; JPO;	2001/08/03 17:02
		insulat\$3 (silicon adj2 oxide))	DERWENT;	
			IBM TDB	
26	26997	((substrate wafer ) and (dielectric	EPO; JPO;	2001/08/03 17:02
		insulat\$3 (silicon adj2 oxide))) and	DERWENT;	
		(implant\$3 dop\$4)	IBM TDB	
27	2563	(((substrate wafer ) and (dielectric	EPO; JPO;	2001/08/03 17:03
		insulat\$3 (silicon adj2 oxide))) and	DERWENT;	
	!	(implant\$3 dop\$4)) and epitaxial	IBM TDB	
28	1341	((((substrate wafer ) and (dielectric	EPO; JPO;	2001/08/03 17:03
		insulat\$3 (silicon adj2 oxide))) and	DERWENT;	
		(implant\$3 dop\$4)) and epitaxial) and	IBM TDB	
		(boron "B")		1
29	849	(11111111111111111111111111111111111111	EPO; JPO;	2001/08/03 17:03
		insulat\$3 (silicon adj2 oxide))) and	DERWENT;	
		(implant\$3 dop\$4)) and epitaxial) and	IBM TDB	
20		(boron "B")) and (phosphrous "P")		
30	56	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	EPO; JPO;	2001/08/03 17:04
		insulat\$3 (silicon adj2 oxide))) and	DERWENT;	
[		(implant\$3 dop\$4)) and epitaxial) and	IBM TDB	
		(boron "B")) and (phosphrous "P")) and		
		(P\$2channel\$2 ("P" adj2 channel)		
		P?channel)		